SKD2803

High-voltage High-current Darlington Transistor Arrays

General Description

The SKD2803 is high-voltage high-current Darlington transistor arrays each containing eight open collector common emitter pairs. Each pair is rated at 500mA. Suppression diodes are included for inductive load driving, the inputs and outputs are pinned in opposition to simplify board layout.

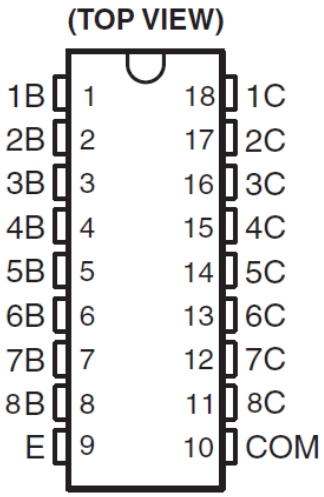
These devices are capable of driving a wide range of loads including solenoids, relays, DC motors, LED displays, filament lamps, thermal print-heads and high-power buffers.

The SKD2803 is available in both a small outline 18-pin package (SOP18).

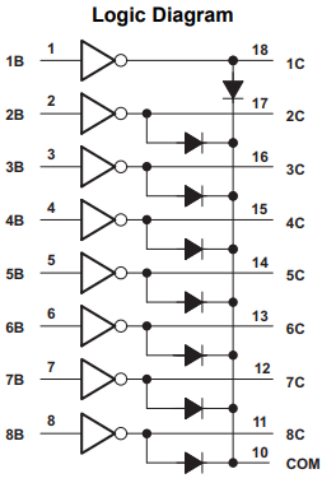
Features

- 500-mA-Rated Collector Current(single output)
- High-Voltage Outputs:50V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay-Driver Applications

Pin Assignments



Connection Diagram



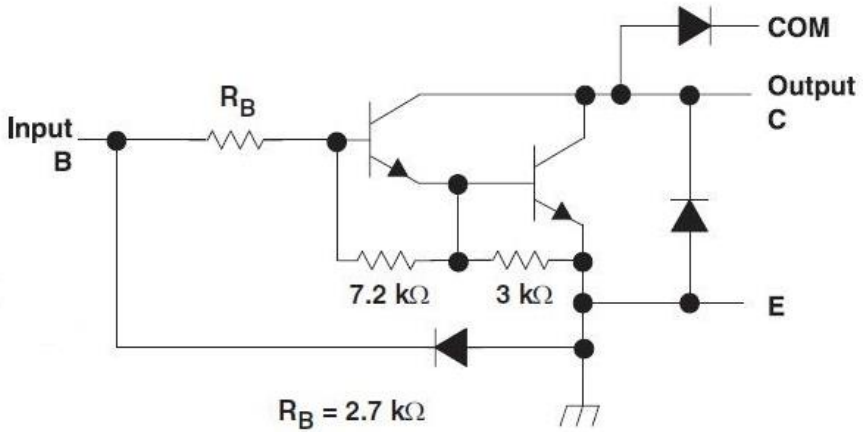
Ordering Information

Order No.	Package	Tape and Reel
SKD2803	SOP18	2000/Reel

Pin Descriptions

Pin Number	Pin Name	Function
1	1B	Input pair1
2	2B	Input pair2
3	3B	Input pair3
4	4B	Input pair4
5	5B	Input pair5
6	6B	Input pair6
7	7B	Input pair7
8	8B	Input pair8
9	E	Common Emitter (ground)
10	COM	Common Clamp Diodes
11	8C	Output pair8
12	7C	Output pair7
13	6C	Output pair6
14	5C	Output pair5
15	4C	Output pair4
16	3C	Output pair3
17	2C	Output pair2
18	1C	Output pair1

Functional Block Diagram



Note: All resistor values shown are nominal.

The collentor-emitter diode is a parasitic structure and should not be used to conduct current.If the collector(s) go below ground an external Schoottky diode should be added to clamp negative undershoots.

Absolute Maximum Ratings (1)

At 25°C free-air temperature (unless otherwise noted)

Symbol	Parameter		Min	Max	Unit
V_{CC}	Collector to emitter voltage			50	V
V_R	Clamp diode reverse voltage(2)			50	V
V_I	Input voltage(2)			30	V
I_{CP}	Peak collector current	See typical characteristics		500	mA
I_{OK}	Output clamp current			500	mA
I_{TE}	Total emitter-terminal current			–2.5	A
T_A	Operating free-air temperature range	SKD2003	–30	+105	℃
θ_{JA}	Thermal Resistance Junction-to-Ambient(3)			63	°C/W
θ_{JC}	Thermal Resistance Junction-to-Case(4)			12	
TJ	Operating virtual junction temperature			150	℃
T_{STG}	Storage temperature range		–40	150	℃

Note:

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

(3) Maximum power dissipation is a function of TJ(max), θJA, and TA. The maximum allowable power dissipation at any allowable ambient temperature is PD = (TJ(max) – TA)/θJA. Operating at the absolute maximum TJ of 150°C can affect reliability.

(4) Maximum power dissipation is a function of TJ(max), θJC, and TA. The maximum allowable power dissipation at any allowable ambient temperature is PD = (TJ(max) – TA)/θJC. Operating at the absolute maximum TJ of 150°C can affect reliability.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
VCC	Collector to Emitter voltage	-	50	V
TA	Operating Ambient Temperature	-30	+105	℃

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Parameter		Test Figure	Test Conditions		MIN	TYP	MAX	Unit
$V_{I(on)}$	On-state input voltage	Figure 6	VCE = 2 V	IC = 200 mA	--	--	2.4	V
				IC = 250 mA	--	--	2.7	
				IC = 300 mA	--	--	3	
$V_{CE(sat)}$	Collector-emitter saturation voltage	Figure 5	II = 250 µA,	IC = 100 mA	--	0.9	1.1	V
			II = 350 µA,	IC = 200 mA	--	1	1.3	
			II = 500 µA,	IC = 350 mA	--	1.2	1.6	
I_{CEX}	Collector cutoff current	Figure 1	VCE = 50 V,	II = 0	--	--	50	µA
		Figure 2	VCE = 50 V, TA = +105℃	II = 0	--	--	100	
V_F	Clamp forward voltage	Figure 8	IF = 350 mA		--	1.7	2	V
$I_{I(off)}$	Off-state input current	Figure 3	VCE = 50 V, IC = 500 µA		50	65	--	µA
II	Input current	Figure 4	VI = 3.85 V		--	0.93	1.35	mA
			VI = 5 V		--	--	--	
			VI = 12 V		--	--	--	
IR	Clamp reverse current	Figure 7	VR = 50 V		--	--	50	µA
				TA = 70°C	--	--	100	
Ci	Input capacitance		VI = 0, f = 1 MHz		--	15	25	pF

Switching Characteristics (TA = +25°C, unless otherwise specified)

Parameter		Test Conditions	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to high-level output	See Figure 9		0.25	1	µs
t_{PHL}	Propagation delay time, high- to low-level output	See Figure 9		0.25	1	µs
V_{OH}	High-level output voltage after switching	VS = 50 V, IO = 300 mA, See Figure 9	VS–20			mV

Parameter Measurement Information

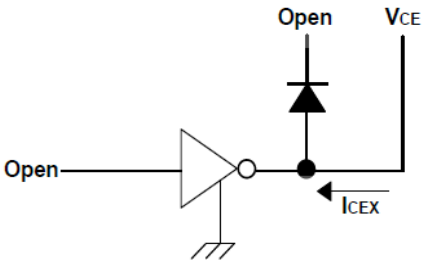

Fig.1 I_{CEX} Test Circuit

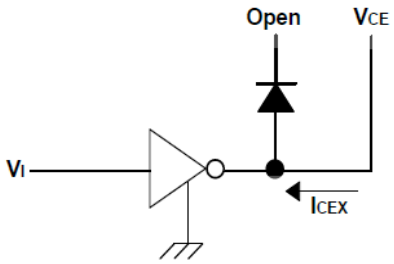

Fig.2 I_{CEX} Test Circuit

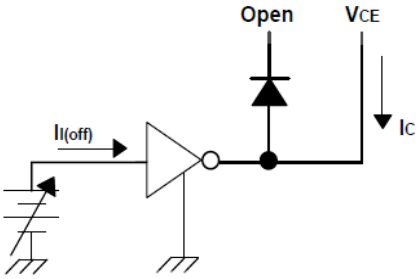

Fig.3 $I_{I(off)}$ Test Circuit

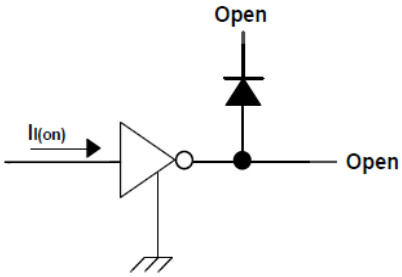

Fig.4 I_I Test Circuit

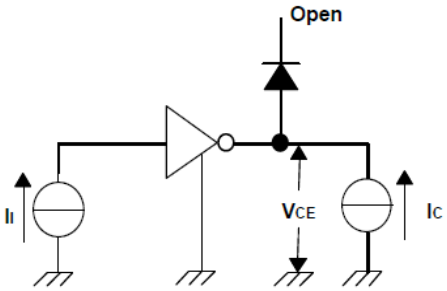

Fig. 5 h_{FE} , $V_{CE(sat)}$ Test Circuit

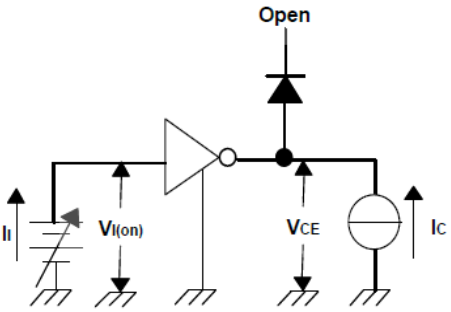

Fig. 6 $V_{I(on)}$ Test Circuit

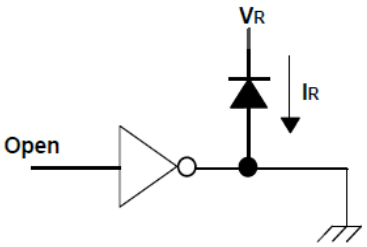

Fig. 7 I_R Test Circuit

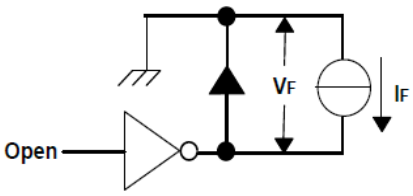

Fig. 8 V_F Test Circuit

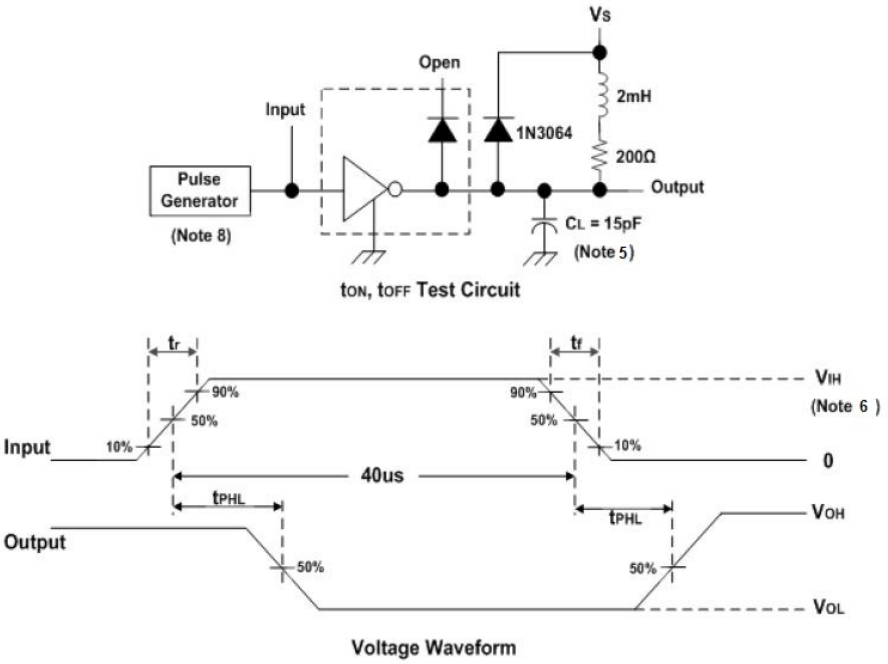

Fig. 9 Latch-Up Test Circuit and Voltage Waveform

Notes: (5). C_L includes prove and jig capacitance.

(6). V_{IH}=3V

SOP18 Outline Dimensions